

# Christoffer Kauppinen

## List of Publications by Year in descending order

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Version: 2024-02-01

19  
papers

291  
citations

1039406

9  
h-index

887659

17  
g-index

19  
all docs

19  
docs citations

19  
times ranked

449  
citing authors

#	ARTICLE	IF	CITATIONS
1	Back-contacted Carrier Injection for Scalable GaN Light Emitters. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2022, 219, 2100461.	0.8	2
2	Grass-like alumina coated window harnesses the full omnidirectional potential of black silicon photodiodes. <i>Applied Optics</i> , 2021, 60, 10415.	0.9	3
3	Superhydrophobic Antireflection Coating on Glass Using Grass-like Alumina and Fluoropolymer. <i>ACS Applied Materials &amp; Interfaces</i> , 2020, 12, 49957-49962.	4.0	51
4	2D electrons and 2D plasmons in AlGaIn/GaN nanostructure under highly non-equilibrium conditions. <i>Journal of Physics: Conference Series</i> , 2020, 1482, 012022.	0.3	0
5	Metalorganic vapor phase epitaxy of wurtzite InP nanowires on GaN. <i>Applied Physics Letters</i> , 2020, 116, 093101.	1.5	2
6	Epi-Gd <sub>2</sub> O <sub>3</sub> /AlGaIn/GaN MOS HEMT on 150- $\mu$ m Si wafer: A fully epitaxial system for high power application. <i>Applied Physics Letters</i> , 2019, 115, 063502.	1.5	14
7	Two-dimensional plasmons in a GaN/AlGaIn heterojunction. <i>Journal of Physics: Conference Series</i> , 2019, 1199, 012014.	0.3	2
8	Site-specific growth of oriented ZnO nanocrystal arrays. <i>Beilstein Journal of Nanotechnology</i> , 2019, 10, 274-280.	1.5	2
9	Selective terahertz emission due to electrically excited 2D plasmons in AlGaIn/GaN heterostructure. <i>Journal of Applied Physics</i> , 2019, 126, .	1.1	26
10	Terahertz Emission due to Radiative Decay of Hot 2D Plasmons in AlGaIn/GaN Heterojunction. , 2019, , .		0
11	MOVPE growth of N-polar AlN on 4H-SiC: Effect of substrate miscut on layer quality. <i>Journal of Crystal Growth</i> , 2018, 487, 12-16.	0.7	20
12	High-Definition Nanoimprint Stamp Fabrication by Atomic Layer Etching. <i>ACS Applied Nano Materials</i> , 2018, 1, 2476-2482.	2.4	7
13	Chemical compatibility of fused filament fabrication-based 3-D printed components with solutions commonly used in semiconductor wet processing. <i>Additive Manufacturing</i> , 2018, 23, 99-107.	1.7	33
14	MOVPE growth of GaN on 6-inch SOI-substrates: effect of substrate parameters on layer quality and strain. <i>Semiconductor Science and Technology</i> , 2017, 32, 045003.	1.0	9
15	Grass-like Alumina with Low Refractive Index for Scalable, Broadband, Omnidirectional Antireflection Coatings on Glass Using Atomic Layer Deposition. <i>ACS Applied Materials &amp; Interfaces</i> , 2017, 9, 15038-15043.	4.0	38
16	Atomic layer etching of gallium nitride (0001). <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2017, 35, .	0.9	37
17	Atomic Layer Engineering of Er-Ion Distribution in Highly Doped Er:Al <sub>2</sub> O <sub>3</sub> for Photoluminescence Enhancement. <i>ACS Photonics</i> , 2016, 3, 2040-2048.	3.2	27
18	Fluorescence-enhancing plasmonic silver nanostructures using azopolymer lithography. <i>RSC Advances</i> , 2016, 6, 48129-48136.	1.7	9

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19	A technique for large-area position-controlled growth of GaAs nanowire arrays. <i>Nanotechnology</i> , 2016, 27, 135601.	1.3	9